Supporting Information

Reduced Electron Relaxation Time of Perovskite Films via g-C_3N_4 Quantum Dots Doping for High-Performance Perovskite Solar Cells

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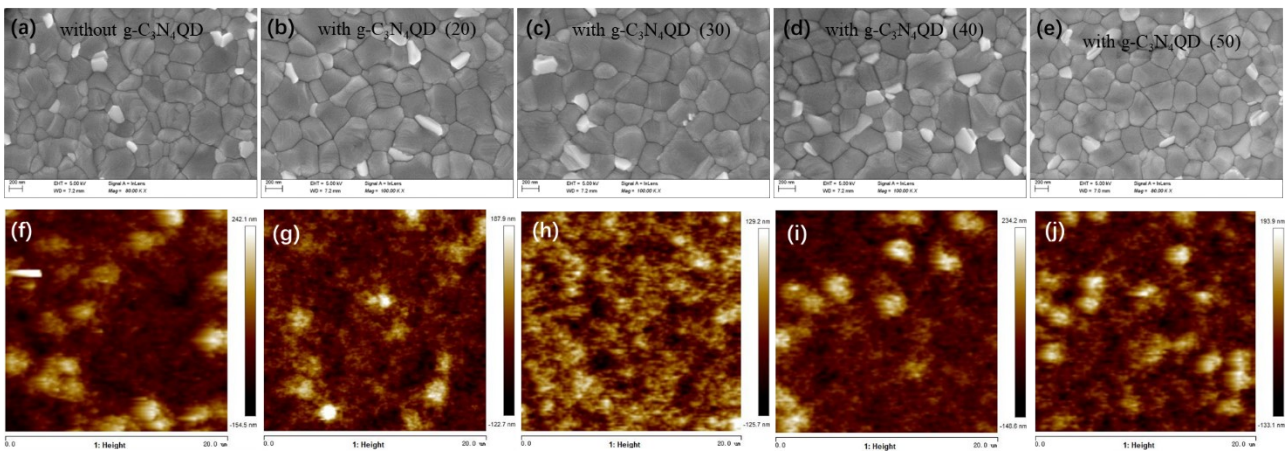

Figure S1. SEM and AFM images of perovskite films with different doping ratios of additives, respectively.

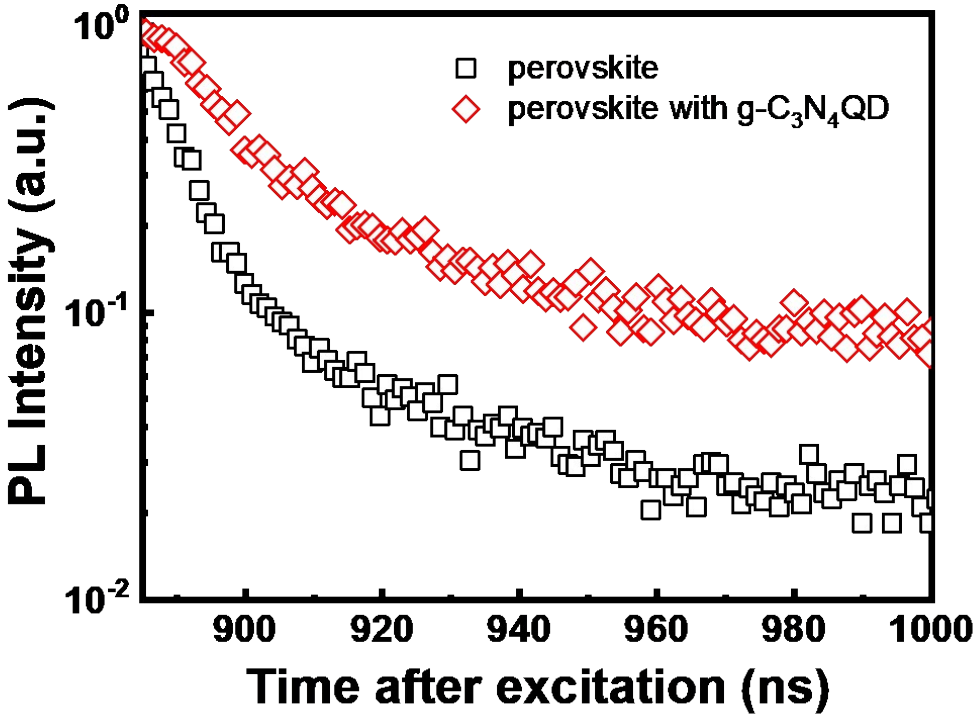

Figure S2. TR PL of perovskite films without and with the optimized concentration of additive (30).

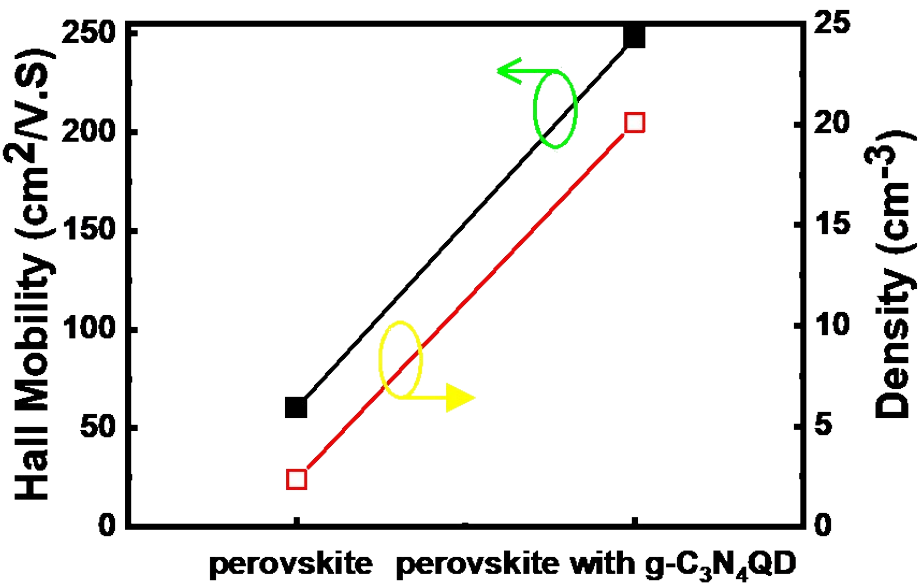

Figure S3. Hall effect of perovskite films without and with the optimized concentration of additive (30).

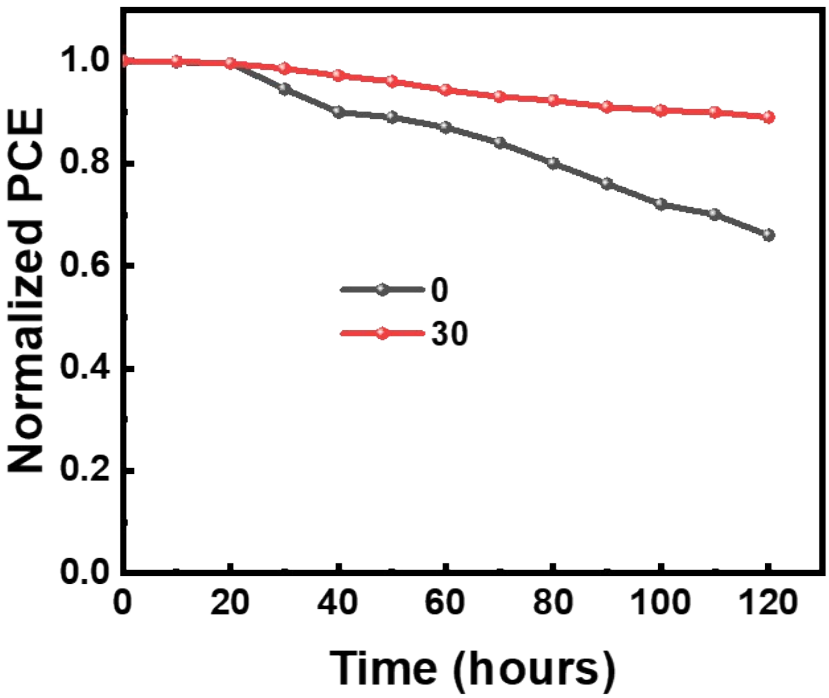

Figure S4. PCE stability test of device with g-C_3N_4QDs (0.4 wt%) and the control device in the air with RH (30%).

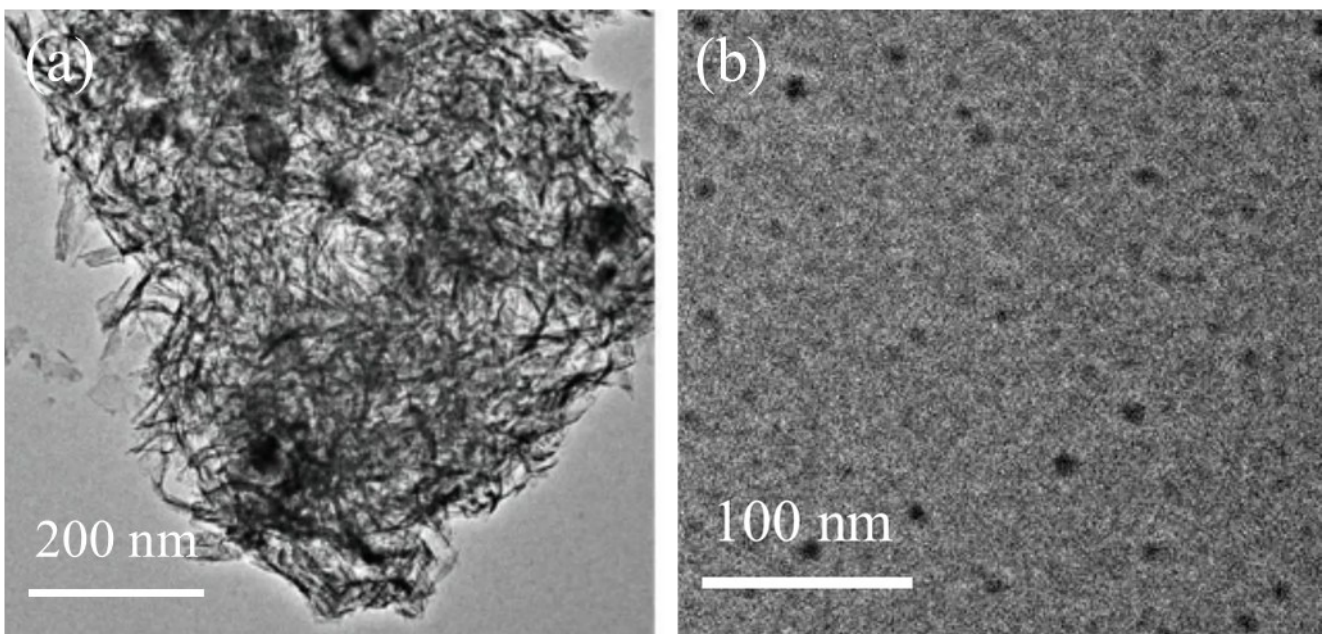

Figure S5. TEM images of (a) g-C_3N_4 nanosheets (b) g-C_3N_4QDs.